

High Voltage Switching Diode

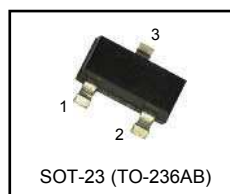
Lead free product

Halogen-free type

FETURE

- We declare that the material of product compliance with RoHS requirements.

BAS21GH



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	250	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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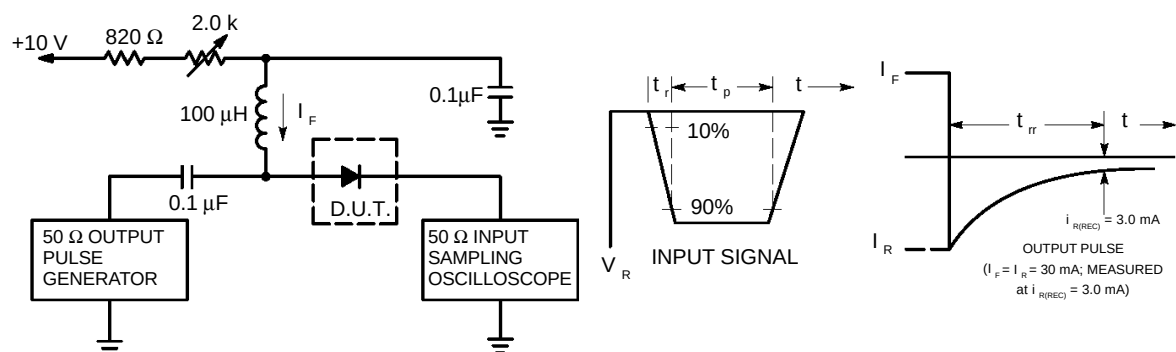
OFF CHARACTERISTICS

Reverse Voltage Leakage Current ($V_R = 200\text{Vdc}$) ($V_R = 200\text{Vdc}, T_J = 150^\circ\text{C}$)	I_R	—	0.1 100	μAdc
Reverse Breakdown Voltage ($I_{BR} = 100\mu\text{Adc}$)	$V_{(BR)}$	250	—	Vdc
Forward Voltage ($I_F = 100\text{mAdc}$) ($I_F = 200\text{mAdc}$)	V_F	—	1000 1250	mV
Diode Capacitance ($V_R = 0, f = 1.0\text{MHz}$)	C_D	—	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30\text{mAdc}, R_L = 100\Omega$)	t_{rr}	—	50	ns

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

Figure 1. Recovery Time Equivalent Test Circuit



- Notes:
1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
 3. $t_p \gg t_r$

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Reel	Reel (pcs)	Carton (pcs)	Packaging
BAS21GH	JS	7"	3,000	60,000 120,000	SOT-23

PACKAGE DIMENSIONS

SOT-23

Unit : mm

